



BSS84Q

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	<b>l</b> <sub>D</sub> Τ <sub>A</sub> = +25°C
-50V	10Ω @ V <sub>GS</sub> = -5V	-130mA

### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BSS84Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

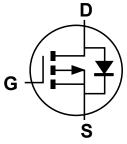
### **Mechanical Data**

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202. Method 208 (a3)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)

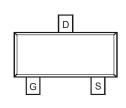




Top View



**Equivalent Circuit** 



Top View

### Ordering Information (Note 4)

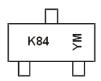
Part Number	Case	Packaging
BSS84Q-7-F	SOT23	3000/Tape & Reel
BSS84Q-13-F	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



## **Marking Information**



K84 = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	1998		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	J		ı	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

# **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-50	V	
Drain-Gate Voltage $R_{GS} \le 20$ kΩ		$V_{DGR}$	-50	V
Gate-Source Voltage	Continuous	$V_{GSS}$	±20	V
Drain Current (Note 5)	Continuous	Ι <sub>D</sub>	-130	mA
Pulsed Drain Current		I <sub>DM</sub>	-1.2	A

# Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	300	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

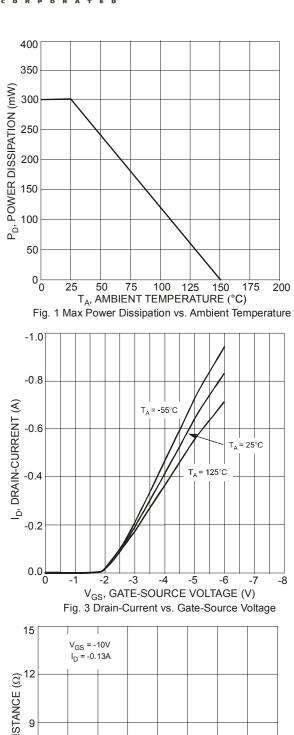
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50	_	_	V	$V_{GS} = 0V$ , $I_D = -250\mu A$	
		_	_	-1	μA	$V_{DS} = -50V$ , $V_{GS} = 0V$ , $T_{J} = +25$ °C	
Zero Gate Voltage Drain Current	$I_{DSS}$	_	_	-2	μA	$V_{DS} = -50V$ , $V_{GS} = 0V$ , $T_{J} = +125$ °C	
		_	—	-100	nA	$V_{DS} = -25V$ , $V_{GS} = 0V$ , $T_{J} = +25$ °C	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(TH)}$	-0.8	_	-2.0	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	3.2	10	Ω	$V_{GS} = -5V$ , $I_D = -0.100A$	
Forward Transconductance	<b>g</b> FS	0.05	_		S	$V_{DS} = -25V$ , $I_{D} = -0.1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	24.6	45	pF		
Output Capacitance	Coss	_	4.7	25	pF	$V_{DS} = -25V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Reverse Transfer Capacitance	Crss	_	2.8	12	pF		
Gate Resistance	$R_g$	_	916	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$	_	0.28	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	0.59	_	nC	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.1A	
Gate-Source Charge	Q <sub>gs</sub>	_	0.09	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	0.08	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10	_	ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18	_	ns	$R_{GEN}$ = 50 $\Omega$ , $V_{GS}$ = -10 $V$	

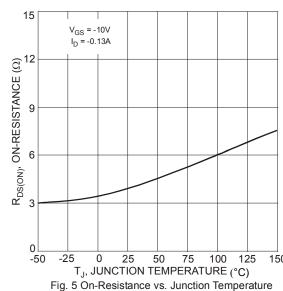
Notes: 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html.

<sup>6.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>7.</sup> Guaranteed by design. Not subject to production testing.







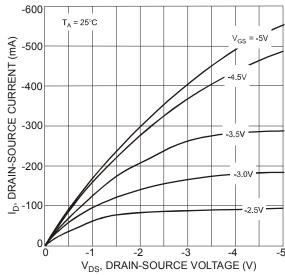
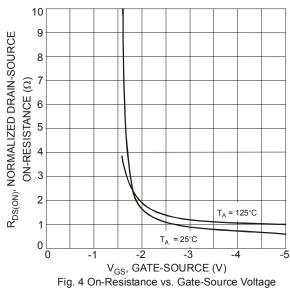


Fig. 2 Drain-Source Current vs. Drain-Source Voltage



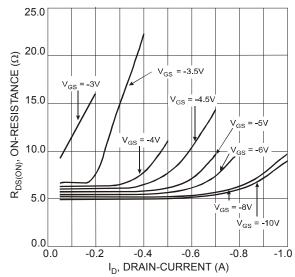
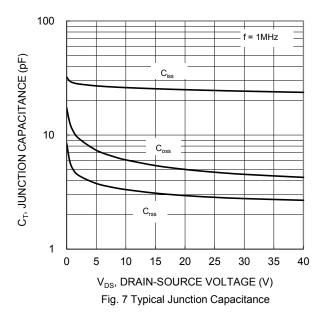
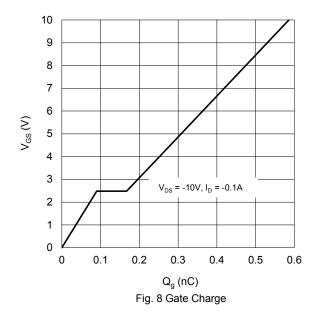
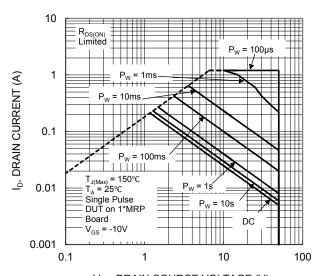


Fig. 6 On-Resistance vs. Drain-Current









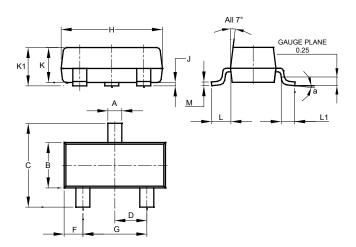
V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Fig. 9 SOA, Safe Operation Area



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

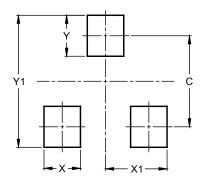


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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